

Dual N-Ch 60V Fast Switching MOSFETs

Description

The HSM1564 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

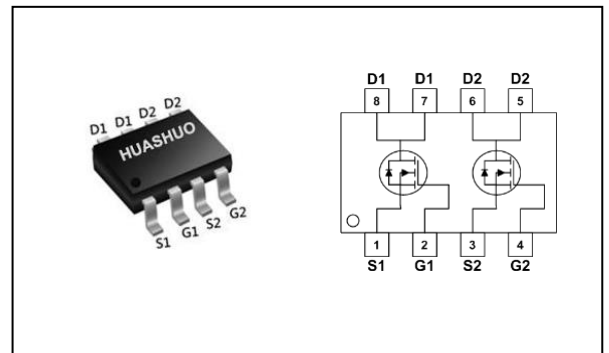
The HSM1564 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	60	V
$R_{DS(ON),TYP}$	13.5	m Ω
I_D	8	A

Dual SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	A
I_{DM}	Pulsed Drain Current ²	32	A
EAS	Single Pulse Avalanche Energy ³	150	mJ
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	24	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =8A	---	13.5	17	mΩ
		V _{GS} =4.5V, I _D =6A	---	15.5	20	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	2	3	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.24	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =8A	18	---	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	3.2	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =30V, V _{GS} =10V, I _D =6A	---	53	---	nC
Q _{gs}	Gate-Source Charge		---	7.5	---	
Q _{gd}	Gate-Drain Charge		---	12	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =3Ω, I _D =4A	---	8	---	ns
T _r	Rise Time		---	5.5	---	
T _{d(off)}	Turn-Off Delay Time		---	29	---	
T _f	Fall Time		---	4.6	---	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	---	2600	---	pF
C _{oss}	Output Capacitance		---	180	---	
C _{rss}	Reverse Transfer Capacitance		---	123	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	8	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

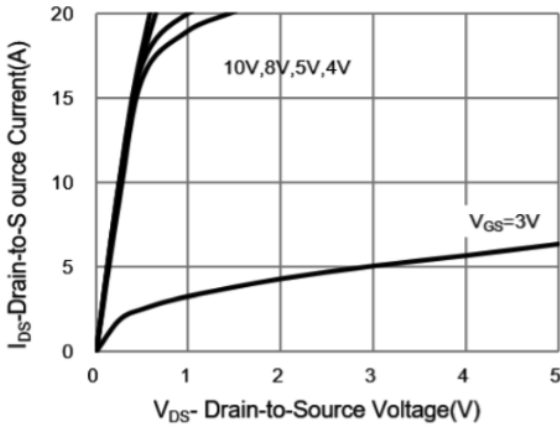


Fig.1 On-Region Characteristics

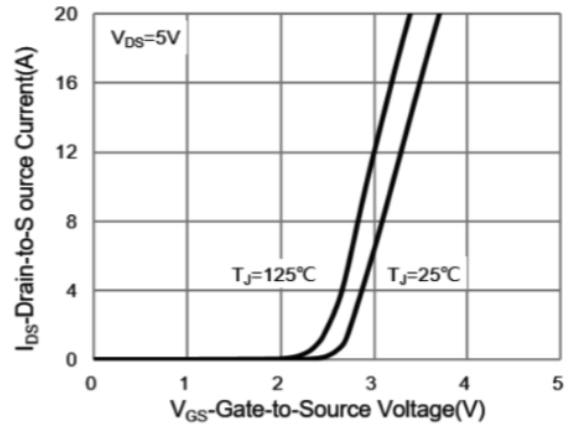


Fig.2 Transfer Characteristics

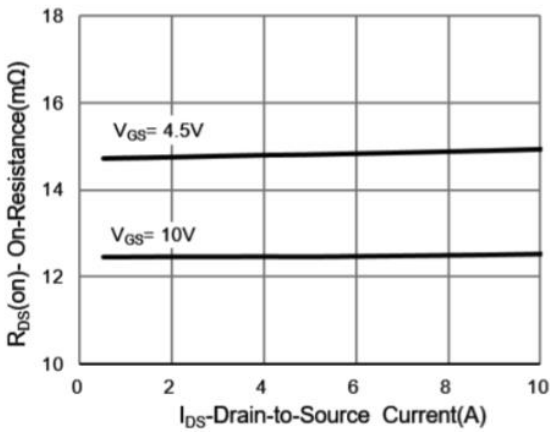


Fig.3 On-Resistance vs. Drain Current and Gate Voltage

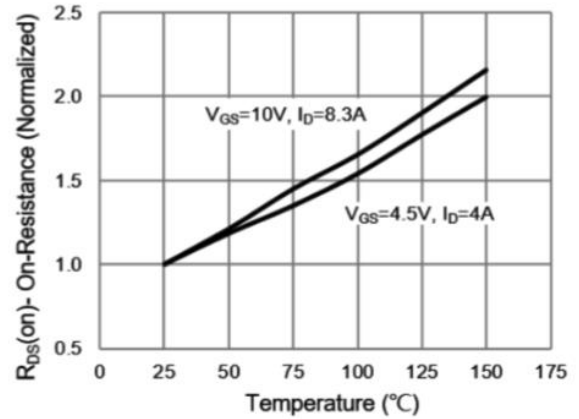


Fig.4 On-Resistance vs. Junction Temperature

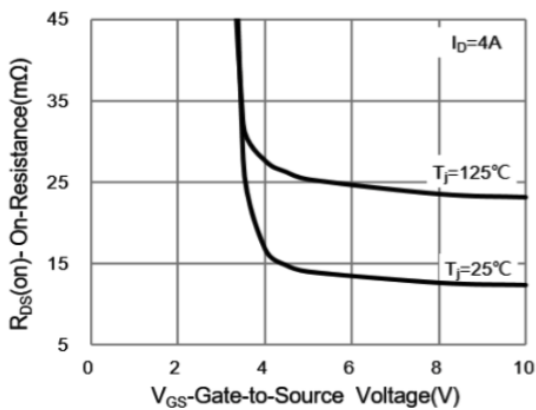


Fig.5 On-Resistance vs. Gate-Source Voltage

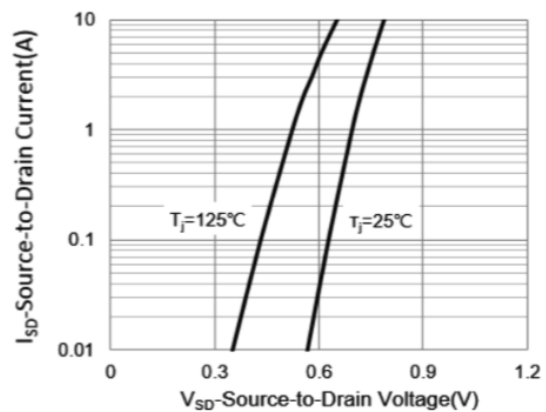


Fig.6 Body-Diode Characteristics



Ordering Information

Part Number	Package code	Packaging
HSM1564	SOP-8	4000/Tape&Reel

